UCN-5832A AND UCN-5832C BIMOS II 32-BIT SERIAL-INPUT, LATCHED DRIVERS

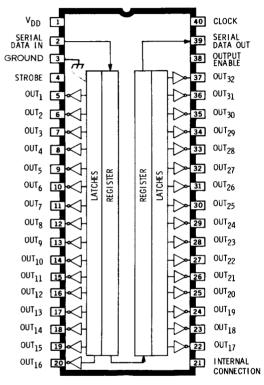
FEATURES

- 5 MHz Typical Data Input Rate
- Low-Power CMOS Logic and Latches
- 40 V Current Sink Outputs
- Low Saturation Voltage

INTENDED PRIMARILY to drive thermal printheads, Types UCN-5832A and UCN-5832C have been optimized for low output-saturation voltage, high-speed operation, and pin/pad configurations most convenient for the tight space requirements of high-resolution printheads. The integrated circuits can also be used to drive multiplexed LED displays or incandescent lamps at up to 150 mA peak current. A combination of bipolar and MOS technologies gives BiMOS II arrays an interface flexibility beyond the reach of standard buffers and power driver circuits.

The devices each have 32 bipolar open-collector saturated drivers, a CMOS data latch for each of the drivers, two 16-bit CMOS shift registers, and CMOS control circuitry. The high-speed CMOS shift registers and latches allow operation with most microprocessor/LSI-based systems. Use of these drivers with TTL may require input pull-up resistors to ensure an input logic high.

Type UCN-5832A is supplied in a 40-pin dual inline plastic package with 0.600" (15.24 mm) row spacing. Under normal operating conditions, all outputs of the packaged device will sustain 100 mA continuously without derating. Type UCN-5832C is an unpackaged, passivated, bare-back device in chip form. In this version, the shift register is divided into two 16-bit blocks for maximum flexibility. For either device, MOS serial outputs permit cascading

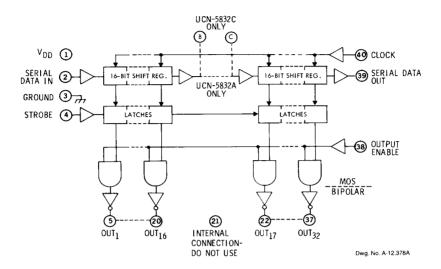


Dwg. No. A-12.377A

for interface applications requiring additional drive lines.

A similar 32-bit serial-input latched source driver is available as UCN-5818A. High-voltage, high-current 8-bit devices are available in Series UCN-5820A.

FUNCTIONAL BLOCK DIAGRAM



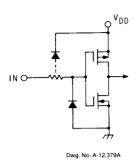
ABSOLUTE MAXIMUM RATINGS at + 25°C Free-Air Temperature

Output Voltage, V _{out}
Logic Supply Voltage, V _{DD}
Input Voltage Range, V_{IN}
Continuous Output Current, I _{OUT}
Package Power Dissipation, Po (UCN-5832A)
Operating Temperature Range, T _A
Storage Temperature Range, T_s

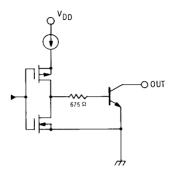
^{*}Derate at the rate of 28 mW/°C above T_A = +25°C

Caution: Sprague CMOS devices have input-static protection but are susceptible to damage when exposed to extremely high static electrical charges.

TYPICAL INPUT CIRCUIT



TYPICAL OUTPUT DRIVER

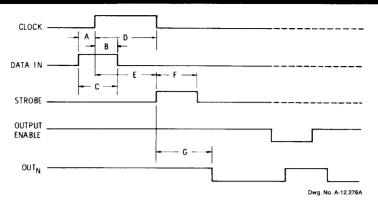


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ELECTRICAL CHARACTERISTICS at $T_A = +25$ °C, $V_{DD} = 5$ V (unless otherwise noted)

				Limits	
Characteristic	Symbol	Test Conditions	Min.	Max.	Units
Output Leakage Current	I _{CEX}	$V_{out} = 40 \text{ V}, T_A = 70^{\circ}\text{C}$		10	μΑ
Collector-Emitter	V _{CE(SAT)}	$I_{out} = 50 \text{ mA}$		275	m۷
Saturation Voltage	ue(shi)	I _{out} = 100 mA	250	550	m۷
Input Voltage	V _{(N(1)}		3.5	5.3	٧
mpat voitage	V _{IN(0)}		-0.3	+ 0.8	٧
Input Current	I _{IN(1)}	$V_{IN} = 3.5 \text{ V}$	_	1.0	μΑ
mpac ourrone	I _{IN(O)}	$V_{IN} = 0.8 \text{ V}$	_	- 1.0	μΑ
Input Impedance	Z _{IN}	$V_{IN} = 3.5 \text{ V}$	3.5		MΩ
Serial Data/Output Resistance	R _{out}		_	20	kΩ
Supply Current	I _{DD}	One output ON, I _{out} = 100 mA	<u> </u>	5.0	mA
ouppi) ouriers	"	All outputs OFF	_	50	μA
Output Rise Time	t,	l _{out} = 100 mA, 10% to 90%		1.0	μs
Output Fall Time	t,	$I_{OUT} = 100 \text{ mA}, 90\% \text{ to } 10\%$		1.0	μs

NOTE: Positive (negative) current is defined as going into (coming out of) the specified device pin.



TIMING CONDITIONS

(Logic Levels are Vpn and Ground)

		$V_{DD} = 5.0 \text{ V}$
A.	Minimum Data Active Time Before Clock Pulse (Data Set-Up Time)	75 ns
B.	Minimum Data Active Time After Clock Pulse (Data Hold Time)	75 ns
C.	Minimum Data Pulse Width	150 ns
D.	Minimum Clock Pulse Width	150 ns
E.	Minimum Time Between Clock Activation and Strobe	300 ns
F.	Minimum Strobe Pulse Width	100 ns
G.	Typical Time Between Strobe Activation and Output Transition	500 ns

SERIAL DATA present at the input is transferred to the shift register on the logic "0" to logic "1" transition of the CLOCK input pulse. On succeeding CLOCK pulses, the registers shift data information towards the SERIAL DATA OUTPUT. The SERIAL DATA must appear at the input prior to the rising edge of the CLOCK input waveform.

Information present at any register is transferred to its respective latch when the STROBE is high (serial-to-parallel conversion). The latches will continue to accept new data as long as the STROBE is held high. Applications where the latches are bypassed (STROBE tied high) will require that the OUTPUT ENABLE input be low during serial data entry.

When the OUTPUT ENABLE input is low, all of the output buffers are disabled (OFF) without affecting the information stored in the latches or shift register. With the OUTPUT ENABLE input high, the outputs are controlled by the state of the latches.

TRUTH TABLE

Serial		Shift Register Contents	Serial		Latch Contents	Output	Output Contents
Data Input	Clock Input	l ₁ l ₂ l ₃ _{N-1} _N	Data Output	Strobe Input	l ₁ l ₂ l ₃ l _{N-1} l _N	Enable Input	
Н		$H R_1 R_2 \dots R_{N-2} R_{N-1}$	R_{N-1}				
L	_	$L R_1 R_2 \dots R_{N-2} R_{N-1}$	R_{N-1}				
X	_	$R_1 R_2 R_3 \dots R_{N-1} R_N$	R _N				
		X X XX X	Х	L	$R_1 R_2 R_3 \dots R_{N-1} R_N$		
		$P_1 P_2 P_3 \dots P_{N-1} P_N$	P _N	Н	$P_1 P_2 P_3 \dots P_{N-1} P_N$	Н	P_1 P_2 P_3 P_{N-1} P_N
					X X XX X	L	й н нн н

L = Low Logic Level

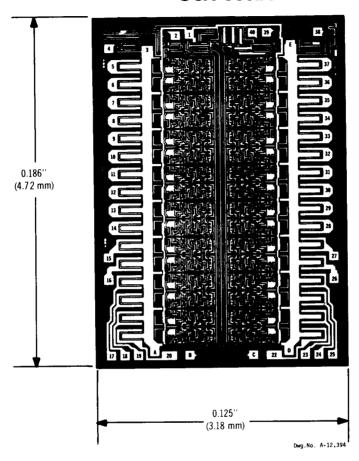
H = High Logic Level

X = Irrelevant

P = Present State

R = Previous State

UCN-5832C



UCN-5832 chips are of silicon planar epitaxial construction. They are identical to those used for packaged devices. When assembled correctly, they should lead to a high final test yield. All chips are visually inspected for masking, diffusion, and scribing defects. Conformance to electrical parameters can be guaranteed (at additional charge) by performing measurements on packaged units assembled from a random sample taken from the lot.

The preferred method of sale for unpackaged die is in wafer form. These are identified as UCN-5832CW and are supplied in 4" (100 mm) wafers that have been tested (probed) in wafer form. Electrically defective devices are identified by ink dots during this operation. Wafers do not include visual die inspection. Orders for UCN-5832CW will be accepted only for complete wafers.

Because Sprague Electric Company does not control the customer packaging of UCN-5832C chips or UCN-5832CW wafers, Sprague Electric company assumes no liability for final electrical and reliability parameters.

	PAD DESIGNATIONS					
PAD	UCN-5832A	UCN-5832C				
1	V _{DD}	V _{DD}				
2	SERIAL DATA IN	SERIAL DATA IN				
3	GROUND	GROUND*				
4	STROBE	STROBE				
5	OUT	OUT,				
6	OUT,	OUT ₂				
7	OUT,	OUT ₃				
8	OUT	OUT ₄				
9	OUT,	OUT,				
10	OUT ₆	OUT ₆				
11	OUT,	OUT,				
12	OUT,					
13	OUT,	TUO.				
14		OUT ₉				
15	OUT.	OUT ₁₀				
16	OUT,1	OUT,1				
	OUT ₁₂	OUT				
17	OUT ₁₃	OUT ₁₃				
18	OUT ₁₄	OUT ₁₄				
19	OUT ₁₅	OUT ₁₅				
A		GROUND*				
20	OUT ₁₆	OUT_{16}				
В		SERIAL DATA OUT				
21	INTERNAL CONNECTION—DO NOT USE	-				
C		SERIAL DATA IN:				
22	OUT ₁₇	OUT ₁₇				
D	_	GROUND*				
23	OUT ₁₈	OUT ₁₈				
24	OUT ₁₉	OUT ₁₉				
25	OUT_{20}	OUT ₂₀				
26	OUT ₂₁	0UT ₂₁				
27	OUT_{22}	OUT ₂₂				
28	OUT ₂₃	OUT ₂₃				
29	OUT ₂₄	OUT ₂₄				
30	OUT ₂₅	OUT ₂₅				
31	0UT ₂₆	OUT ₂₆				
32	OUT ₂₇	OUT ₂₇				
33	OUT ₂₈	0UT ₂₈				
34	OUT ₂₉	0UT ₂₉				
35	OUT ₃₀	OUT ₃₀				
36	OUT ₃₁	OUT ₃₁				
37	OUT ₃₂					
38	OUTPUT ENABLE	OUT ₃₂ OUTPUT ENABLE				
E	OUT OF CHABLE					
39	SERIAL DATA OUT	GROUND*				
39 40		SERIAL DATA OUT ₃				
łU	CLOCK	CLOCK				

^{*}Bonding pads A or 3 and D or E must be connected to the substrate. For maximum output current capability, pads A, D, E, and 3 must all be bonded to the substrate.